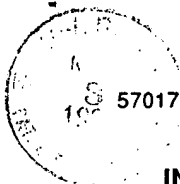


10/Pre 10



57017.P025C

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

CHEN, J. et al.

Examiner: Mosley, T.

Bet
1-4-93

Serial No.:

Art Unit: 1503

Filing Date:

For: METHOD TO IMPROVED
LITHOGRAPHIC PATTERNING IN A
SEMICONDUCTOR FABRICATION
PROCESS

Continuation Application of:

Serial No.: 07/863,791

Filed: April 6, 1992

Preliminary Amendment

Box Non-fee Amendments (Pats)
Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sirs:

Prior to the examination of the above-identified application, please
amend the application as follows:

IN THE CLAIMS:

1. (Amended Twice) In a [A] method [of] for lithographically transferring [printing a two-dimensional feature] a pattern from a mask into a radiation-sensitive material deposited over a semiconductor substrate [on a substrate] utilizing an imaging tool, said pattern including a feature having first and second edges, each of said first and second edges having associated edge gradients, said first and second edges being spaced in close proximity to one another such that said associated edge gradients interact causing said feature